

Please type a plus sign (+) inside this box →

PTO/SB/08A (10-96)

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information if it contains a valid OMB control number.

Substitute for form 1449A/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	09/857,859
		Filing Date	06/11/2001
		First Named Inventor	Dr. Bernd HEINEMANN
		Group Art Unit	
		Examiner Name	
Sheet	1	of	2
		Attorney Docket Number	
		7040-30	

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>3</sup>	Number <sup>4</sup>			
IN	BA	DE	42 40 738	A1	Mahnkopf	08/26/1993
IN	BB	DE	1 764 313		Barson	05/25/1972
IN	BC	DE	41 02 888	A1	Hamasaki	08/01/1991
IN	BD	EP	0 552 561	A3	Turner	07/28/1993
IN	BE	EP	0 818 829	A1	Oda	01/14/1998
IN	BF	EP	0 529 772	A1	Streit	03/03/1993
IN	BG	EP	0 551 185	A2	Morizuka	07/14/1993
IN	BH	EP	0 795 899	A1	Koenig	09/17/1997
IN	BI	WO	98/26457	A1	Lippert	06/18/1998
IN	BJ	FR	2 693 839	A1	Stephane	01/21/1994

Examiner Signature	J. NGUYEN	Date Considered	7/18/03
-----------------------	-----------	--------------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

**Burden Hour Statement:** This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.



Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet

1

of

1

**C mplete if Known**

Application Number	09/857,859
Filing Date	06/11/2001
First Named Inventor	Dr. Bernd HEINEMANN
Group Art Unit	
Examiner Name	
Attorney Docket Number	7040-30

**OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TM	CA	COMFORT, ET AL, "Single Crystal Emitter Cap for Epitaxial Si and SiGe-base Transistors," IEDM, IEEE (USA), p. 857-60, ( December 11, 1991).	
TM	CB	GRUHLE, ET AL, "Low 1/f noise SiGe HBTs with application to low phase noise microwave oscillators," Electronics Letters, Vol. 33 ( No. 24), p. 2050-52, ( November 20, 1997).	
TM	CC	CHANTRE, ET AL, "A high performance low complexity SiGe HBT for BiCMOS integration," IEEE BCTM, IEEE (USA),	
TM	CD	CHO, ET AL, "A 42-GHz (fmax) SiGe-Base HBT using reduced pressure CVD," Solid State Electronics, Elsevier (Great Britain), Vol. 42 ( No. 0), p. 1641-49, ( August 23, 1998).	
TM	CE	LOMBARDO, ET AL, "Band-Gap Narrowing and High Frequency Characteristics of Si/GeSi Heterojunction Bipolar Transistors Formed by Ge Ion Implantation in Si," Transactions on Electronic Devices, IEEE (USA), Vol. 45 ( No. 7), p. 1531-37, ( July 23, 1998).	
TM	CF	BENSAHEL, ET AL., "Single wafer processing of in situ doped polycrystalline Si and SiGe," Solid State Technology, p. S5-S10, ( March 23, 1998).	
TM	CG	HOPE, "Real-time control of layer thickness in LPCVD Si/Si88Ge12 HBT structures," Thin Solid Films, Elsevier (Great Britain), No. 294, p. 18-21, ( August 23, 1997).	
TM	CH	HUETING, ET AL, "On the optimization of SiGe-Base Bipolar Transistors," Transactions on Electron Devices, IEEE (US), Vol. 43 ( No. 9), p. 1518-24, ( September 23, 1996).	

Examiner  
Signature

T. HEINEMANN

Date  
Considered

7/11/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Unique citation designation number. 2 Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.